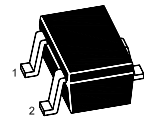
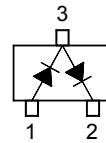


MMBD217SEW

Silicon Epitaxial Planar Switching Diode

Applications

- Ultra high speed switching



SOT-323 Plastic Package
Marking Code: A7

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current (Single)	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current (Single)	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current ($t = 1\text{ }\mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_d	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 70\text{ V}$	I_R	0.1	μA
Capacitance between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$	C_T	3.5	pF
Reverse Recovery Time at $I_F = 5\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 50\text{ }\Omega$	t_{rr}	4	ns

